MA3XD17

Silicon epitaxial planar type

For rectification

For protection against reverse current

■ Features

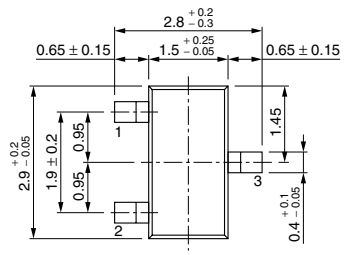
- Mini type 3-pin package
- High breakdown voltage V_R = 100 V

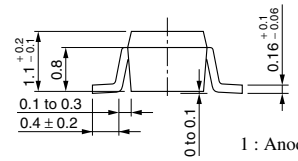
■ Absolute Maximum Ratings T_a = 25°C

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	100	V
Peak reverse voltage	V_{RM}	100	V
Non-repetitive peak forward surge current*	I_{FSM}	1.5	A
Average forward current	$I_{F(AV)}$	300	mA
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	−55 to +150	°C

Note) * : The peak-to-peak value in one cycle of 50 Hz sine-wave (non-repetitive)

Unit : mm

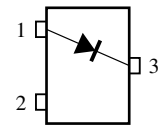




1 : Anode
2 : NC
3 : Cathode
Mini Type Package (3-pin)

Marking Symbol: M5K

Internal Connection



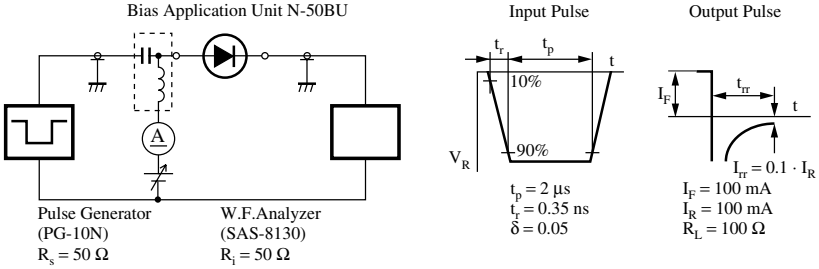
■ Electrical Characteristics T_a = 25°C ± 3°C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_R	V_R = 100 V			200	μA
Forward voltage (DC)	V_F	I_F = 300 mA		0.50	0.58	V
Terminal capacitance	C_t	V_R = 0 V, f = 1 MHz		100		pF
Reverse recovery time*	t_{rr}	$I_F = I_R$ = 100 mA $I_{rr} = 0.1 \cdot I_R$, R_L = 100 Ω		7		ns

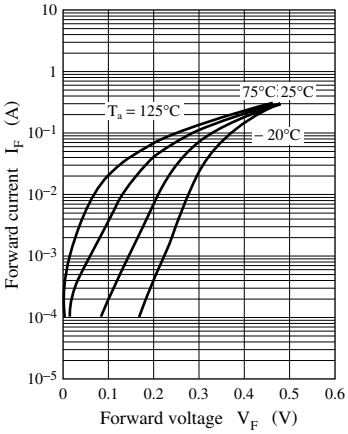
Note) 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on the charge of a human body and the leakage of current from the operating equipment.

1. Rated input/output frequency: 250 MHz

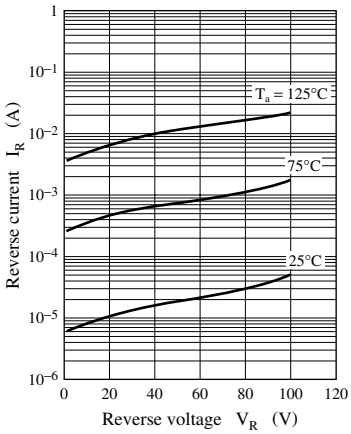
3. * : t_{rr} measuring circuit



I_F — V_F



I_R — V_R



C_t — V_R